

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1-10. (Canceled)

11. (Currently amended) ~~The pattern formation method of Claim 10;~~ A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a base polymer for generating acid is carboxylic acid or sulfonic acid through irradiation with light.

12. (Canceled)

13. (Currently amended) ~~The pattern formation method of Claim 12;~~ A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating acid is carboxylic acid or sulfonic acid through irradiation with light and a base polymer for generating sulfonic acid through irradiation with light.

14. (Canceled)

15. (Currently amended) The pattern formation method of Claim [[10]] 11,

wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

16. (Currently amended) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating sulfonic acid through irradiation with light.

17-18. (Canceled)

19. (Currently amended) The pattern formation method of Claim [[15]] 16,

wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

20. (Currently amended) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes an acid, and
wherein said acid is formic acid.

21. (Canceled)

22. (Original) The pattern formation method of Claim 20,

wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr
laser, Ar₂ laser, Kr₂ laser or extreme UV.

23. (New) The pattern formation method of Claim 11,

wherein the base polymer for generating sulfonic acid through irradiation with light is an
ester of polyvinylsulfonic acid or polystyrenesulfonic acid.

24. (New) The pattern formation method of Claim 13,

wherein the base polymer for generating sulfonic acid through irradiation with light is an
ester of polyvinylsulfonic acid or polystyrenesulfonic acid.

25. (New) The pattern formation method of Claim 11,

wherein the base polymer for generating sulfonic acid through irradiation with light is
poly(styrenesulfonic acid-t-butyl ester) or poly(styrenesulfonic acid-2-methyl-2-adamantyl
ester).

26. (New) The pattern formation method of Claim 13,

wherein the base polymer for generating sulfonic acid through irradiation with light is
poly(styrenesulfonic acid-t-butyl ester) or poly(styrenesulfonic acid-2-methyl-2-adamantyl
ester).

27. (New) The pattern formation method of Claim 13,

wherein the dissolution inhibitor for generating sulfonic acid through irradiation with light is an ester of styrenesulfonic acid.

28. (New) The pattern formation method of Claim 16,

wherein the dissolution inhibitor for generating sulfonic acid through irradiation with light is an ester of styrenesulfonic acid.

29. (New) The pattern formation method of Claim 13,

wherein the dissolution inhibitor for generating sulfonic acid through irradiation with light is styrenesulfonic acid-t-butyl ester or styrenesulfonic acid-2-methyl-2-adamantyl ester.

30. (New) The pattern formation method of Claim 16,

wherein the dissolution inhibitor for generating sulfonic acid through irradiation with light is styrenesulfonic acid-t-butyl ester or styrenesulfonic acid-2-methyl-2-adamantyl ester.

31. (New) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a base polymer for generating carboxylic acid through irradiation with light, and

wherein the base polymer for generating carboxylic acid through irradiation with light is an ester of polyacrylic acid, polymethacrylic acid or poly(α -trifluoromethylacrylic acid).

32. (New) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating carboxylic acid through irradiation with light, and

wherein the dissolution inhibitor for generating carboxylic acid through irradiation with light is an ester of acrylic acid, methacrylic acid or α -trifluoromethylacrylic acid.

33. (New) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating carboxylic acid through irradiation with light and a base polymer for generating carboxylic acid through irradiation with light, and

wherein the dissolution inhibitor for generating carboxylic acid through irradiation with light is an ester of acrylic acid, methacrylic acid or α -trifluoromethylacrylic acid, and the base polymer for generating carboxylic acid through irradiation with light is an ester of polyacrylic acid, polymethacrylic acid or poly(α -trifluoromethylacrylic acid).

34. (New) The pattern formation method of Claim 27, wherein the base polymer for generating carboxylic acid through irradiation with light is poly(t-butyl acrylate), poly(methoxymethyl acrylate), poly(ethoxymethyl acrylate), poly(2-methyl-2-adamantyl acrylate), poly(t-butyl methacrylate), poly(methoxymethyl methacrylate), poly(ethoxymethyl methacrylate), poly(2-methyl-2-adamantyl methacrylate), poly(t-butyl- α -trifluoromethyl acrylate), poly(methoxymethyl- α -trifluoromethyl acrylate), poly(ethoxymethyl- α -trifluoromethyl acrylate) or poly(2-methyl-2-adamantyl- α -trifluoromethyl acrylate).

35. (New) The pattern formation method of Claim 29, wherein the base polymer for generating carboxylic acid through irradiation with light is poly(t-butyl acrylate), poly(methoxymethyl acrylate), poly(ethoxymethyl acrylate), poly(2-methyl-2-adamantyl acrylate), poly(t-butyl methacrylate), poly(methoxymethyl methacrylate), poly(ethoxymethyl methacrylate), poly(2-methyl-2-adamantyl methacrylate), poly(t-butyl- α -trifluoromethyl acrylate), poly(methoxymethyl- α -trifluoromethyl acrylate), poly(ethoxymethyl- α -trifluoromethyl acrylate) or poly(2-methyl-2-adamantyl- α -trifluoromethyl acrylate).

36. (New) The pattern formation method of Claim 28, wherein the dissolution inhibitor for generating carboxylic acid through irradiation with light is t-butyl acrylate, methoxymethyl acrylate, ethoxymethyl acrylate, 2-methyl-2-adamantyl acrylate, t-butyl methacrylate, methoxymethyl methacrylate, ethoxymethyl methacrylate, 2-methyl-2-adamantyl methacrylate, t-butyl- α -trifluoromethyl acrylate, methoxymethyl- α -trifluoromethyl acrylate, ethoxymethyl- α -trifluoromethyl acrylate or 2-methyl-2-adamantyl- α -trifluoromethyl acrylate.

37. (New) The pattern formation method of Claim 29, wherein the dissolution inhibitor for generating carboxylic acid through irradiation with light is t-butyl acrylate, methoxymethyl acrylate, ethoxymethyl acrylate, 2-methyl-2-adamantyl acrylate, t-butyl methacrylate, methoxymethyl methacrylate, ethoxymethyl methacrylate, 2-methyl-2-adamantyl methacrylate, t-butyl- α -trifluoromethyl acrylate, methoxymethyl- α -trifluoromethyl acrylate, ethoxymethyl- α -trifluoromethyl acrylate or 2-methyl-2-adamantyl- α -trifluoromethyl acrylate.

38. (New) The pattern formation method of Claim 13, wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

39. (New) The pattern formation method of Claim 31, wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

40. (New) The pattern formation method of Claim 32, wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

41. (New) The pattern formation method of Claim 33, wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.